STD12N65M2

N-channel 650 V, 0.42 Ω typ., 8 A MDmesh M2 Power MOSFET in a DPAK package

Datasheet - production data

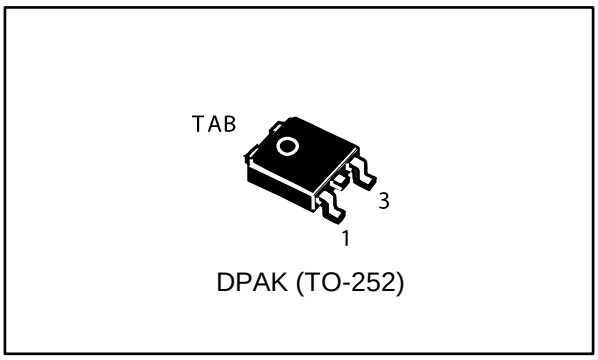
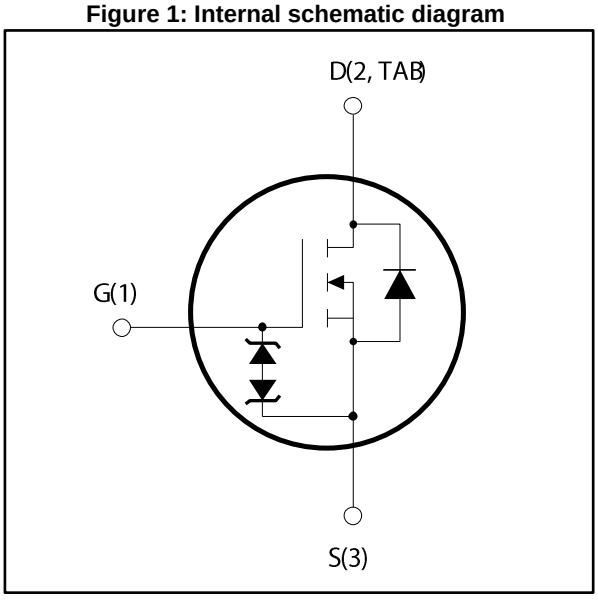


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$max.	I_D
STD12N65M2	650 V	0.5 Ω	8 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STD12N65M2	12N65M2	DPAK	Tape and reel

This is information on a product in full production.

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	8	A
I_D	Drain current (continuous) at T_C = 100 °C	5	A
I_{DM} (1)	Drain current (pulsed)	32	A
P_{TOT}	Total dissipation at T_C = 25 °C	85	W
dv/dt (2)	Peak diode recovery voltage slope	15	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Operating junction temperature		

Notes:

(1)Pulse width limited by safe operating area.

(2)I_{SD} ≤ 8 A, di/dt ≤ 400 A/µs; $V_{DS\ peak}$ < $V_{(BR)DSS}$, V_{DD} = 400 V.

(3)V_{DS} ≤ 520 V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	1.47	°C/W
$R_{thj\text{-}pcb}$	Thermal resistance junction-pcb max (1)	50	°C/W

Notes:

(1)When mounted on 1 inch² FR-4, 2 Oz copper board.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetetive or not repetetive (pulse width limited by T_{jmax})	1.6	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}; V_{DD} = 50 V)	250	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 5: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	650			V
I_{DSS}	Zero gate voltage drain current	V_{GS}= 0 V, V_{DS} = 650 V			1	µA
		V_{GS} = 0 V, V_{GSDS} = 650 V T_C = 125 °C			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 4 A		0.42	0.5	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DS}= 100 V, f = 1 MHz	-	535	-	pF
C_{oss}	Output capacitance		-	25	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 to 520 V	-	144	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, open drain	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 520 V, I_D = 8 A, V_{GS} = 10 V (see *Figure 15: "Gate charge test circuit"*)	-	16.5	-	nC
Q_{gs}	Gate-source charge		-	2.6	-	nC
Q_{gd}	Gate-drain charge		-	8.5	-	nC

Notes:

(1)$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 325 V, I_D = 4 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14: "Switching times test circuit for resistive load"* and *Figure 19: "Switching time waveform"*)	-	9	-	ns
t_r	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off-delay time		-	34	-	ns
t_f	Fall time		-	13.5	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		8	A
I_{SDM} (1)	Source-drain current (pulsed)		-		32	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 8 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V (see *Figure 16: " Test circuit for inductive load switching and diode recovery times"*)	-	313		ns
Q_{rr}	Reverse recovery charge		-	2.7		µC
I_{RRM}	Reverse recovery current		-	17		A
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see *Figure 16: " Test circuit for inductive load switching and diode recovery times"*)	-	462		ns
Q_{rr}	Reverse recovery charge		-	4.1		µC
I_{RRM}	Reverse recovery current		-	17.5		A

Notes:

(1)Pulse width is limited by safe operating area

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

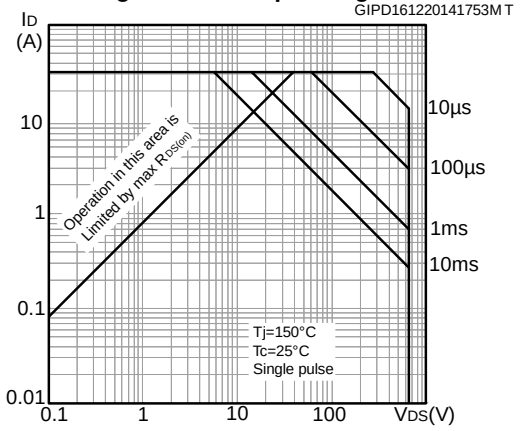


Figure 3: Thermal impedance

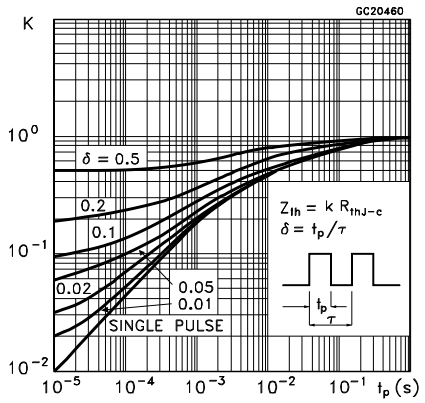


Figure 4: Output characteristics

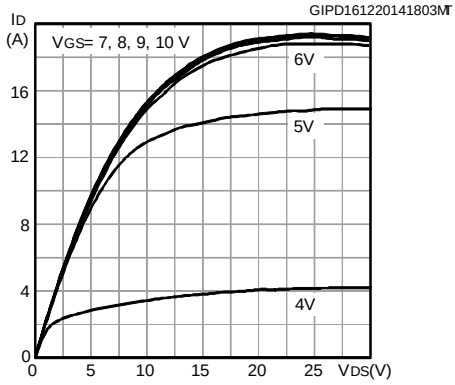


Figure 5: Transfer characteristics

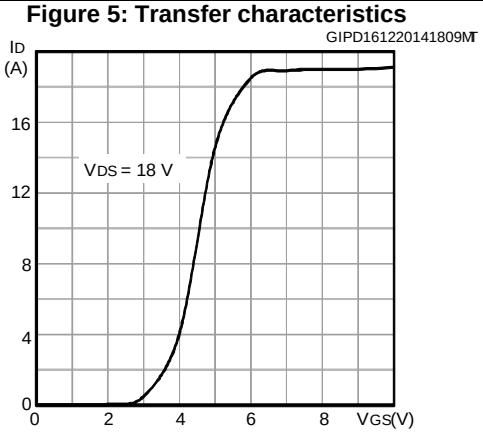


Figure 6: Normalized gate threshold voltage vs temperature

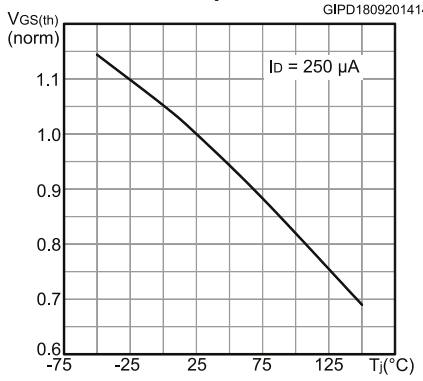


Figure 7: Normalized V (BR)DSS vs. temperature

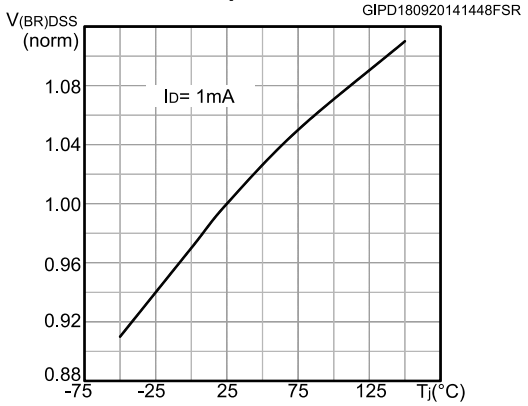


Figure 8: Static drain-source on-resistance

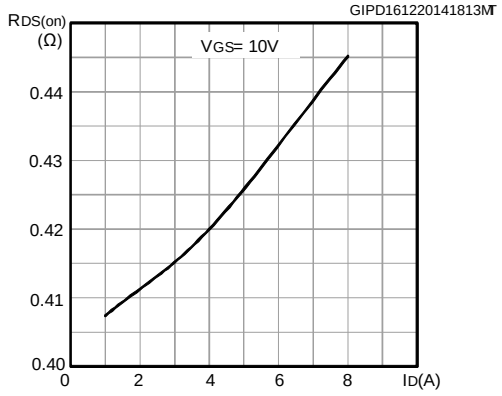


Figure 9: Normalized on-resistance vs temperature

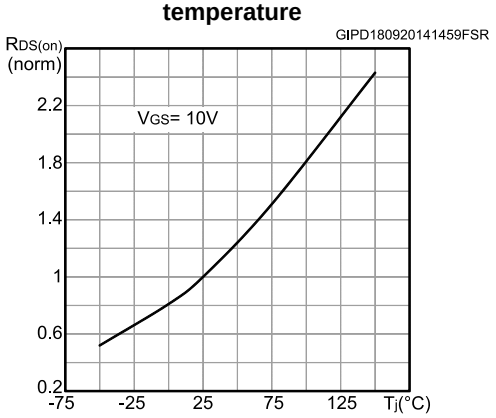


Figure 10: Gate charge vs. gate-source voltage

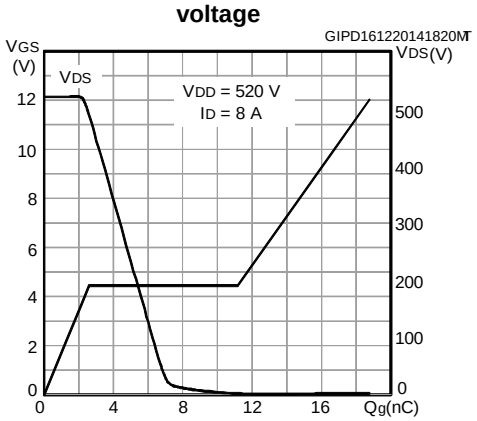


Figure 11: Capacitance variations

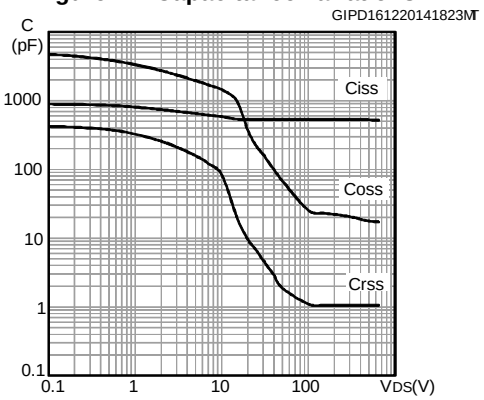


Figure 12: Turn-off switching loss vs drain current

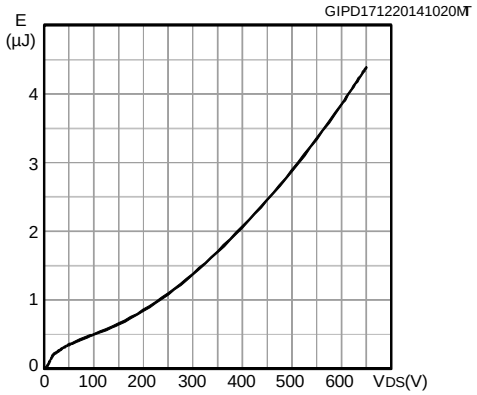
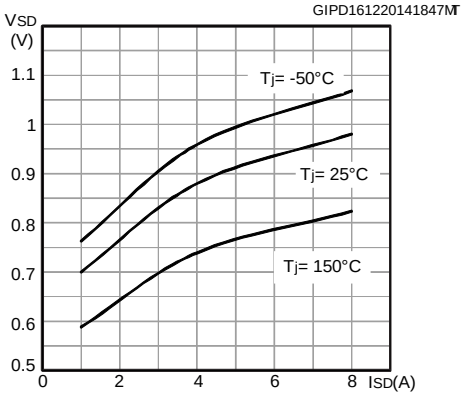


Figure 13: Source-drain diode forward characteristic



3 Test circuits

Figure 14: Switching times test circuit for resistive load

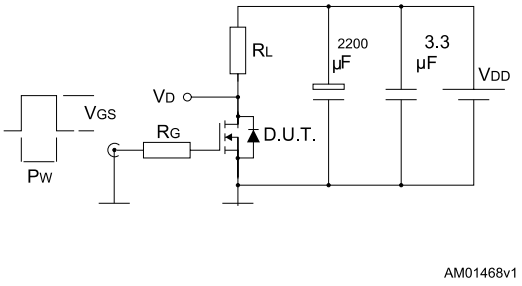


Figure 15: Gate charge test circuit

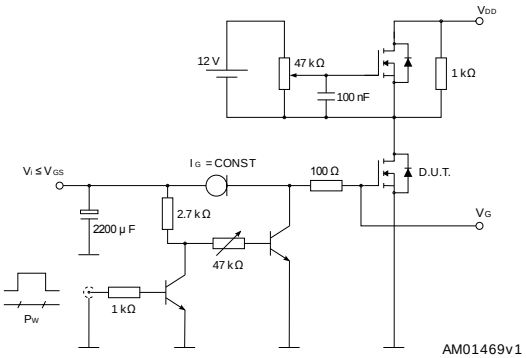


Figure 16: Test circuit for inductive load switching and diode recovery times

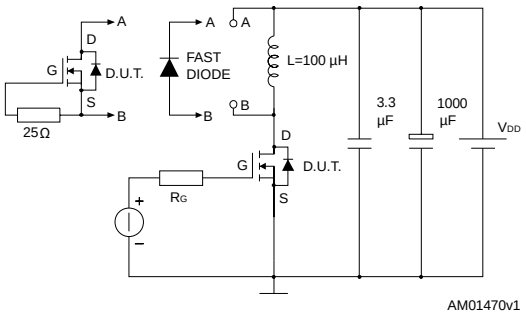


Figure 17: Unclamped inductive load test circuit

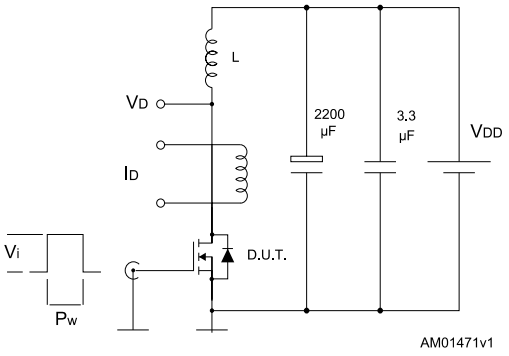


Figure 18: Unclamped inductive waveform

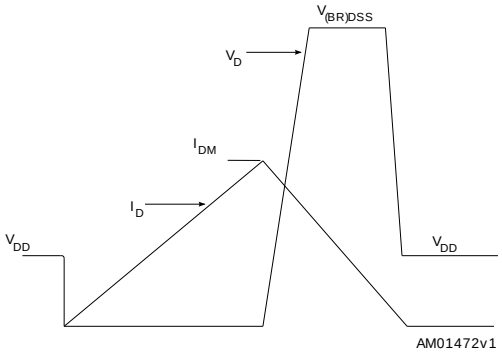
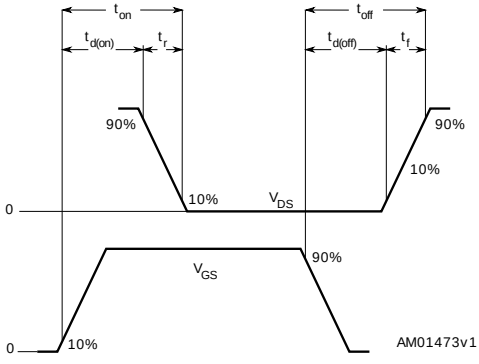


Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 20: DPAK (TO-252) type A package outline

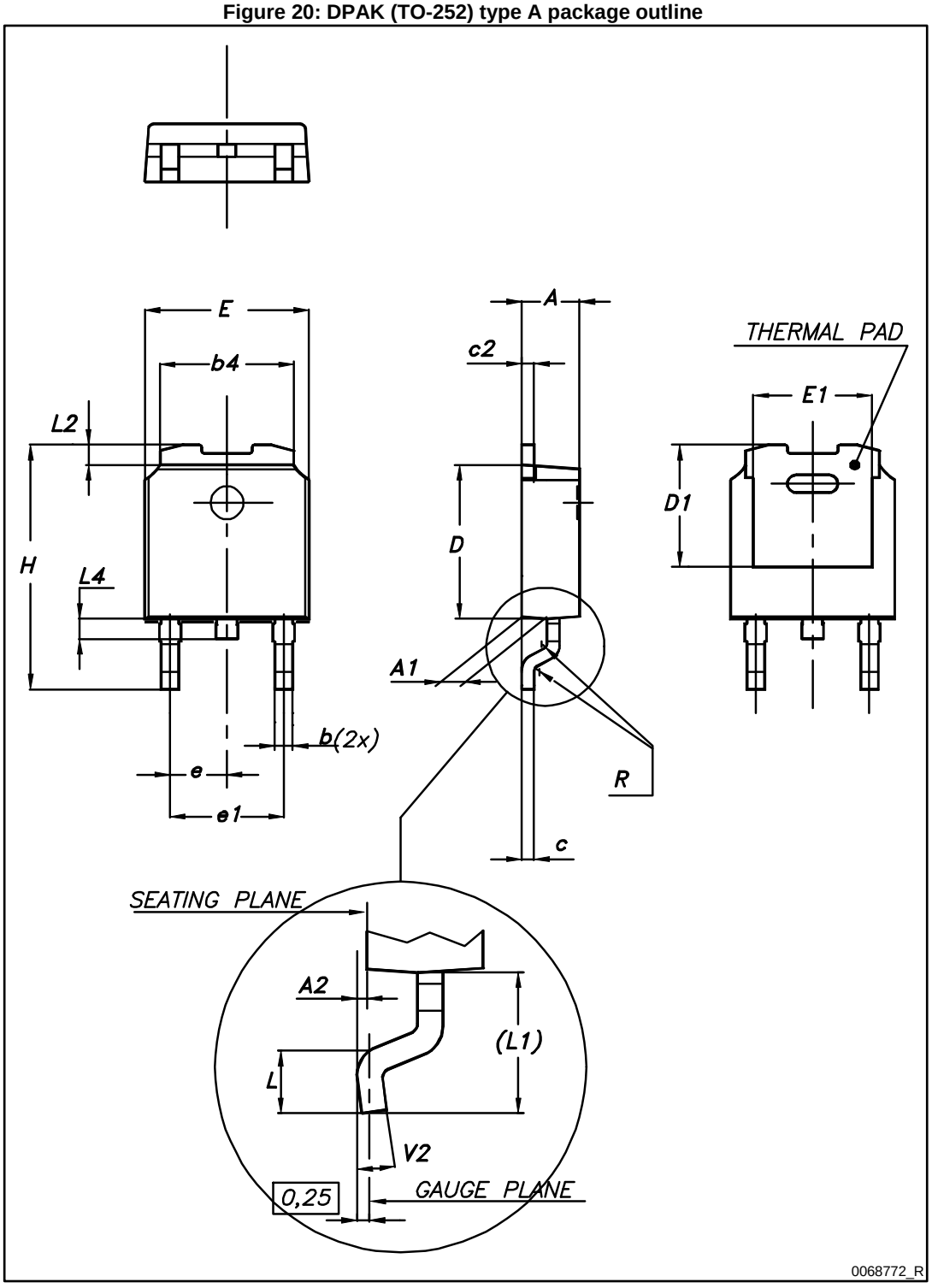
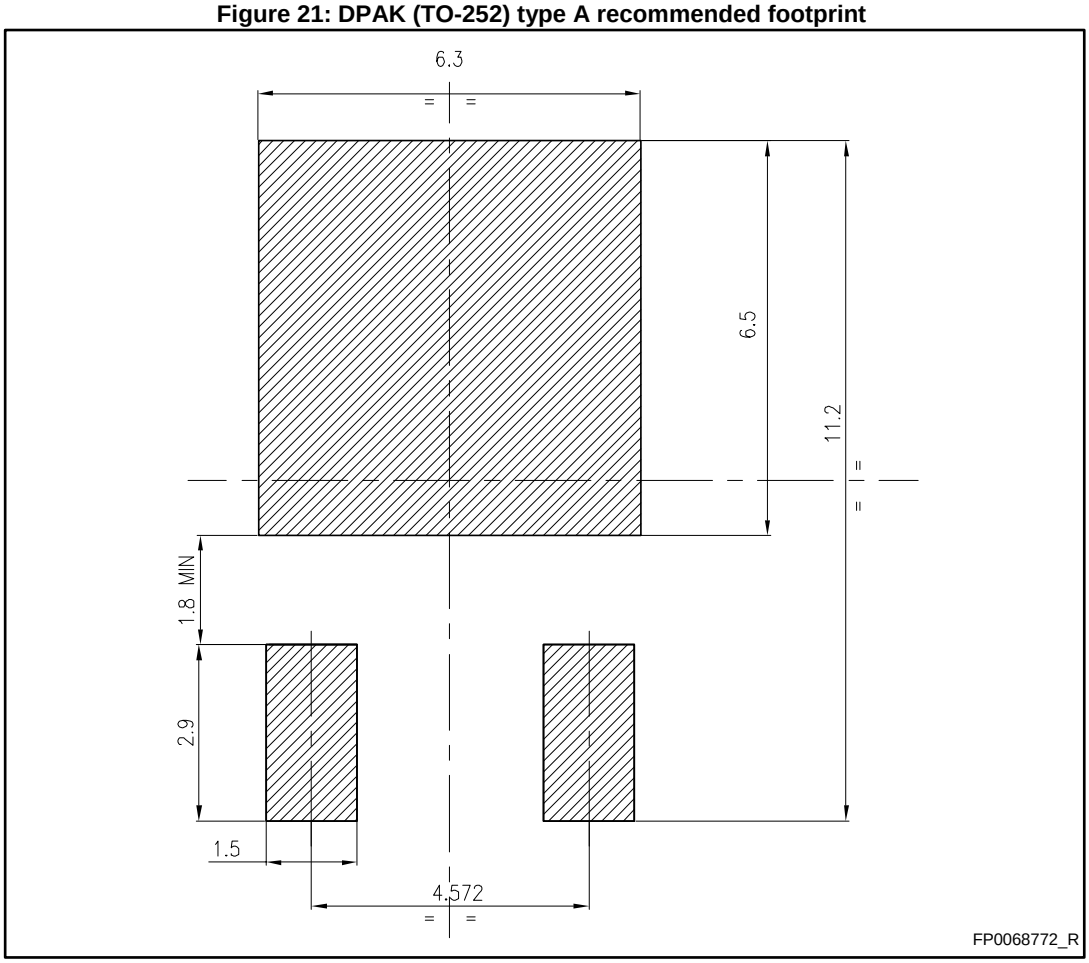


Table 9: DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 21: DPAK (TO-252) type A recommended footprint



All dimensions are in mm

4.2 DPAK (TO-252) packing information

Figure 22: Tape for DPAK (TO-252)

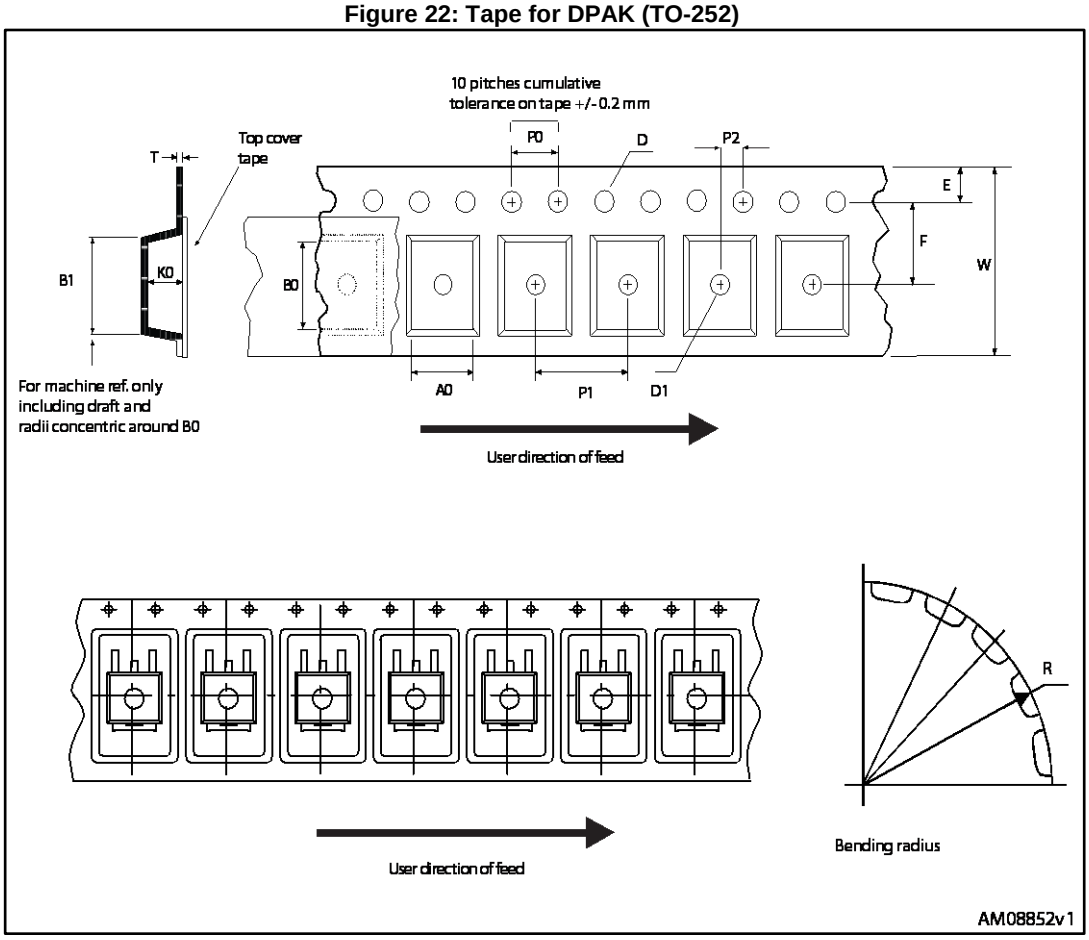


Figure 23: Reel for DPAK (TO-252)

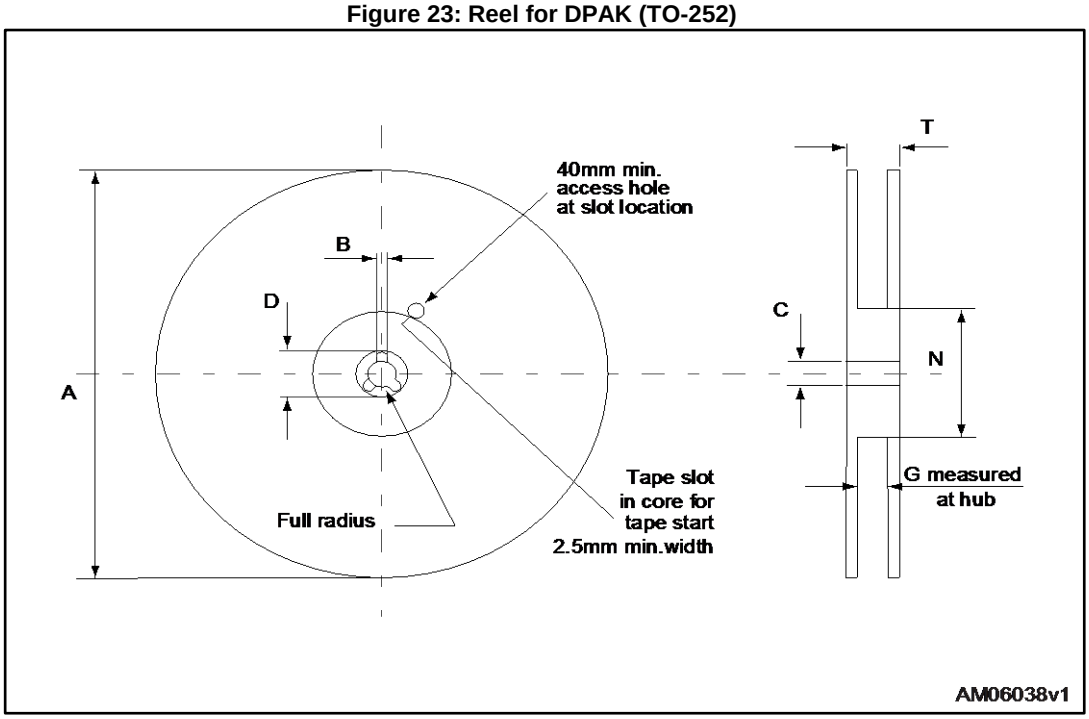


Table 10: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
16-Dec-2014	1	First release.
12-Feb-2015	2	Updated features in cover page. Updated *Table 4: "Avalanche characteristics"*, *Table 7: "Switching times"*, *Figure 2: "Safe operating area"* and *Section 5.1: "DPAK (TO-252) type A package information"*. Minor text changes.

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